

Parameter		Value (ern Curn50)	
V_{DS}			V
V_{GS}			V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	150
		$T_C = 100^\circ\text{C}$	95
I_{DM}	Pulsed Drain Current ⁽¹⁾		600
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾		210
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	89
R_{JA}	Thermal Resistance, Junction to Ambient ⁽³⁾		56
R_{JC}	Thermal Resistance, Junction to Case		1.40
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150

Test Circuit

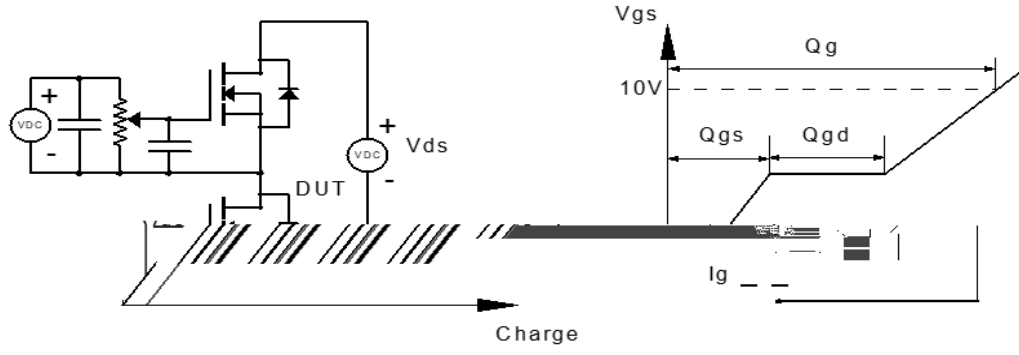


Figure 1: Gate Charge Test Circuit & Waveform

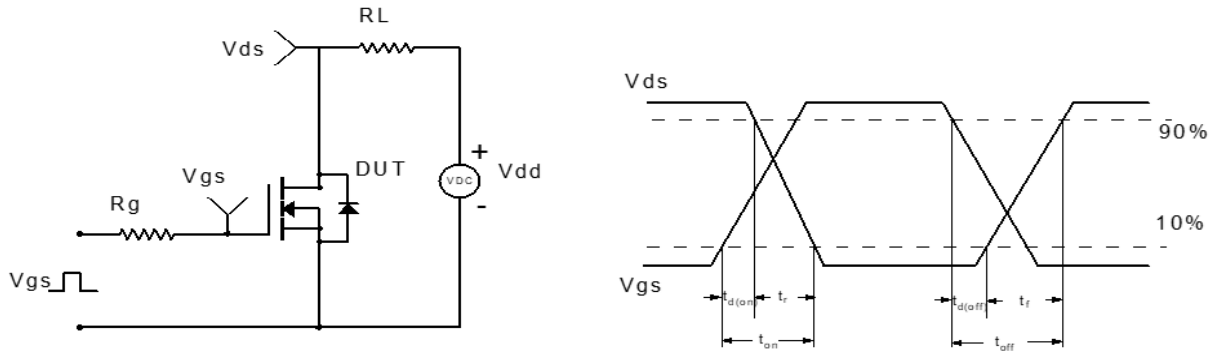


Figure 2: Resistive Switching Test Circuit & Waveform

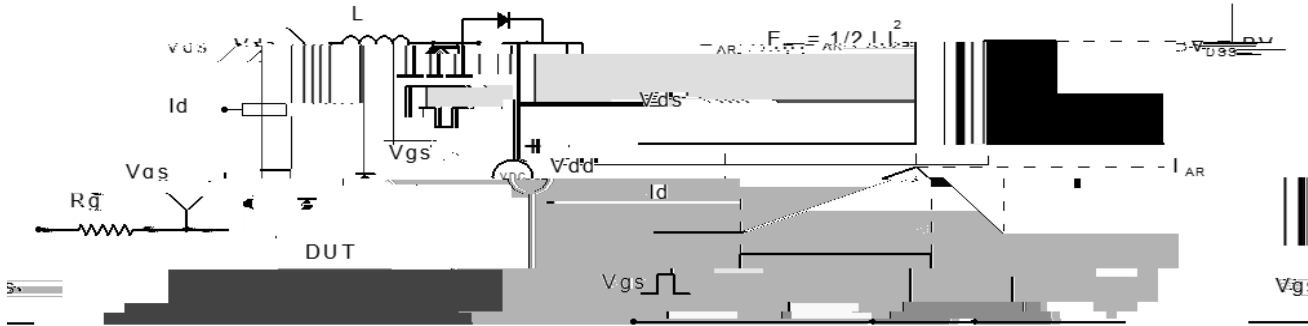


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

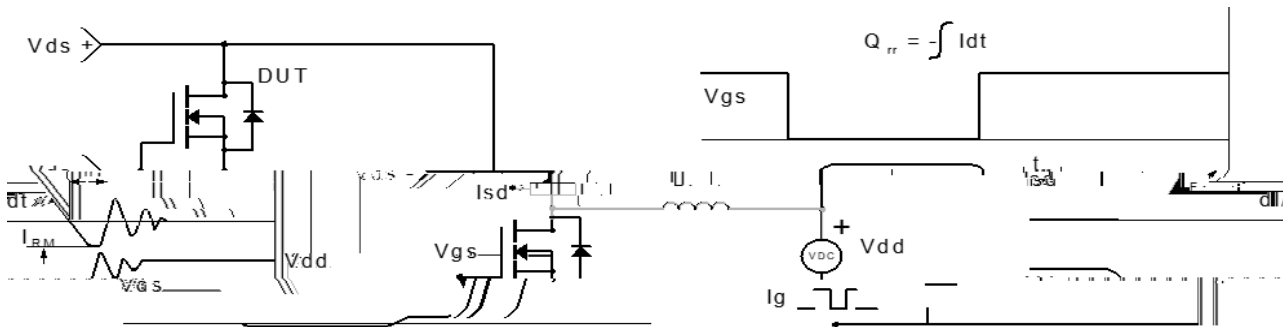


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-220C-3L)



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